

PSMN004-60P/60B

N-channel enhancement mode field-effect transistor

Rev. 01 — 26 April 2002

Product data

1. Description

N-channel logic level field-effect power transistor in a plastic package using TrenchMOS™ technology.

Product availability:

PSMN004-60P in SOT78 (TO-220AB)

PSMN004-60B in SOT404 (D²-PAK).

2. Features

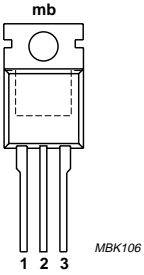
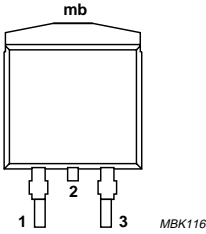
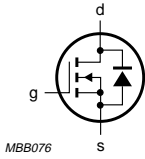
- Low on-state resistance
- Fast switching.

3. Applications

- High frequency computer motherboard DC to DC converters
- OR-ing applications.

4. Pinning information

Table 1: Pinning - SOT78 and SOT404, simplified outline and symbol

Pin	Description	Simplified outline	Symbol	
1	gate (g)			
2	drain (d) [1]			
3	source (s)			
mb	drain (d)			
		SOT78 (TO-220AB)	SOT404 (D ² -PAK)	

[1] It is not possible to make connection to pin 2 of the SOT404 package.

5. Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Typ	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	60	V
I_D	drain current (DC)	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V}$	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$	-	230	W
T_j	junction temperature		-	175	°C
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C}$	3.1	3.6	mΩ

6. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

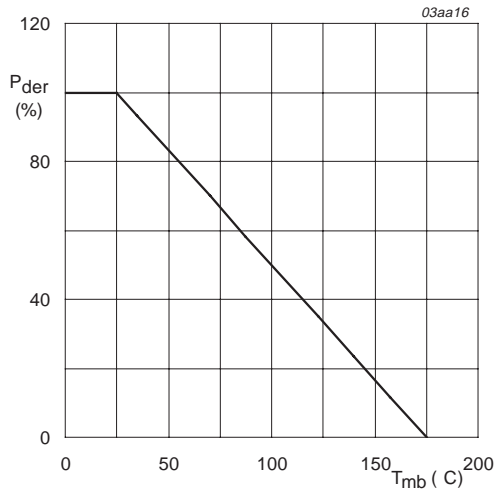
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	60	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	60	V
V_{GS}	gate-source voltage (DC)		-	±20	V
V_{GSM}	gate-source voltage	$t_p \leq 50\text{ }\mu\text{s}$; pulsed; duty cycle 25%; $T_j \leq 150\text{ °C}$	-	±30	V
I_D	drain current (DC)	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V}$; Figure 2 and 3 $T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V}$; Figure 2	-	75	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Figure 3	-	400	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Figure 1	-	230	W
T_{stg}	storage temperature		-55	+175	°C
T_j	junction temperature		-55	+175	°C

Source-drain diode

I_S	source (diode forward) current (DC)	$T_{mb} = 25\text{ °C}$	-	75	A
I_{SM}	peak source (diode forward) current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	400	A

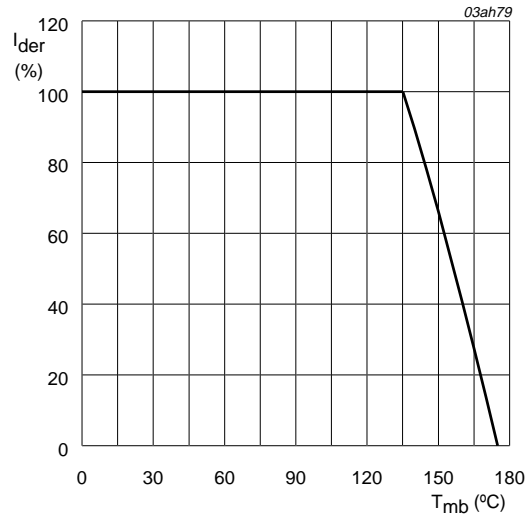
Avalanche ruggedness

$E_{DS(AL)S}$	non-repetitive avalanche energy	unclamped inductive load; $I_D = 75\text{ A}; t_p = 0.1\text{ ms}; V_{DD} = 15\text{ V};$ $R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V};$ starting $T_j = 25\text{ °C}$	-	500	mJ
$I_{DS(AL)S}$	non-repetitive avalanche current	unclamped inductive load; $V_{DD} = 15\text{ V}; R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V};$ starting $T_j = 25\text{ °C}$	-	75	A



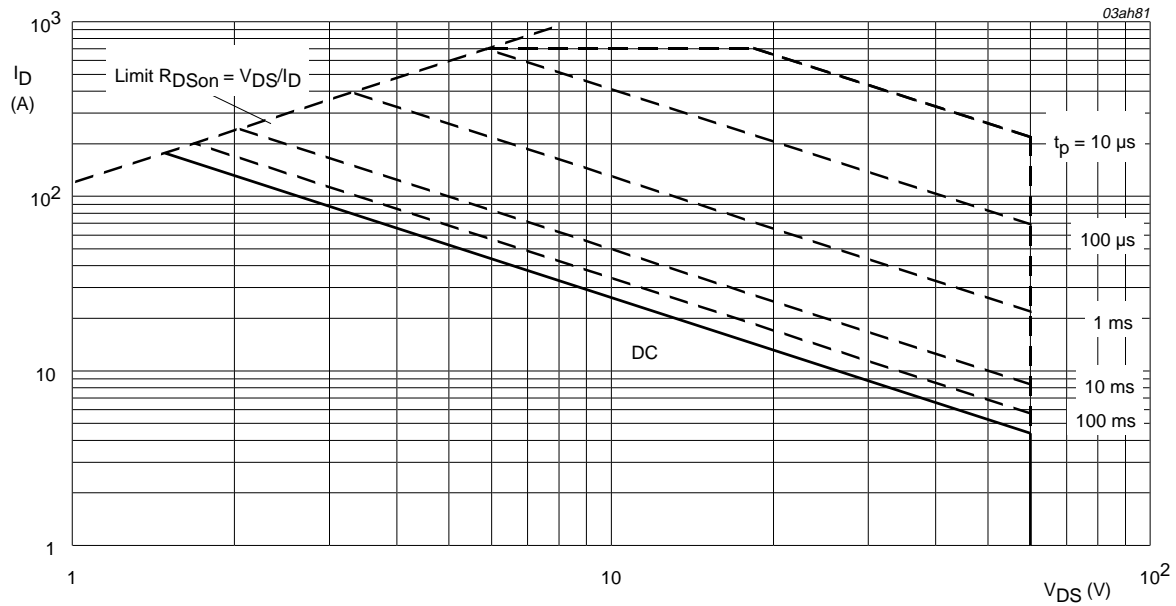
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature.



T_{mb} = 25 °C; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

7. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient					
	SOT78	vertical in still air	-	-	60	K/W
	SOT404	mounted on a printed circuit board; minimum footprint	-	-	50	K/W

7.1 Transient thermal impedance

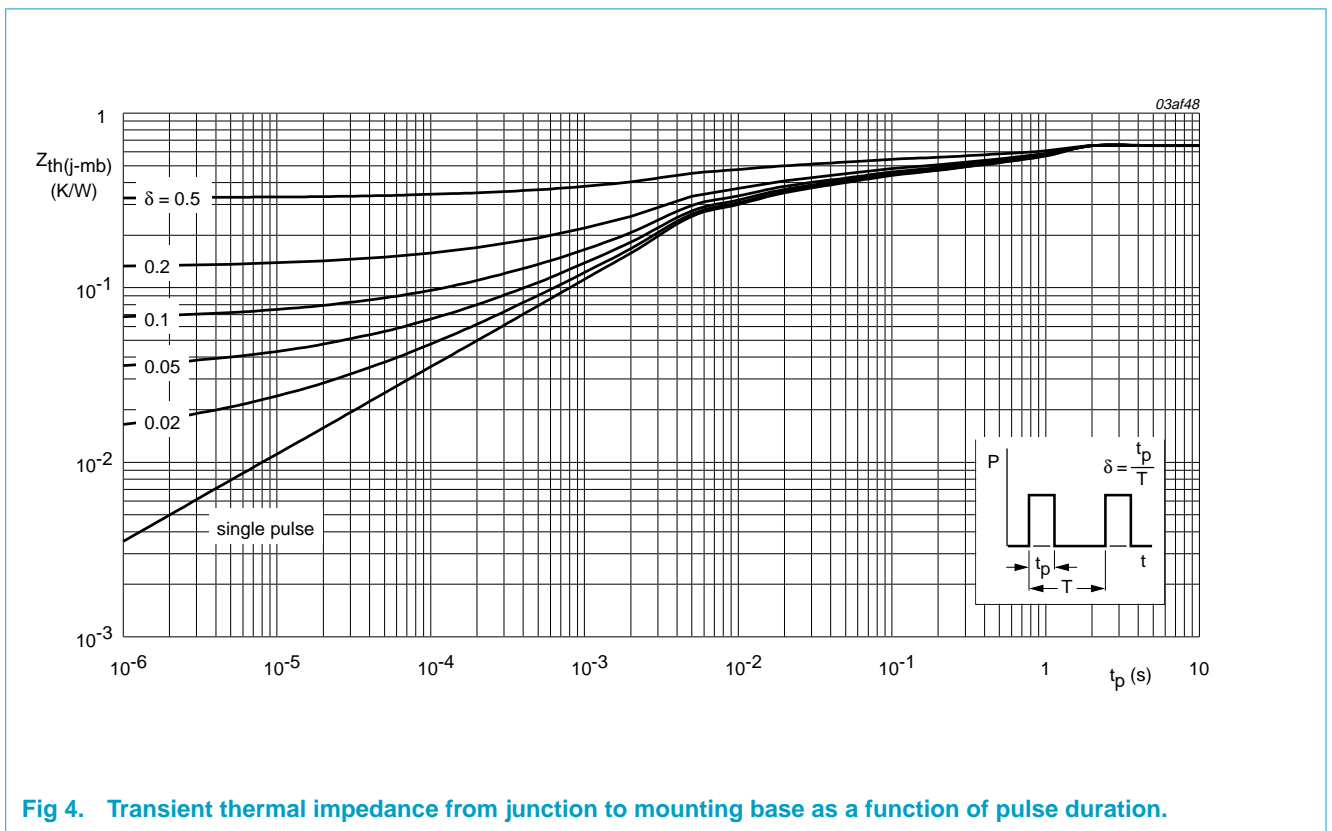
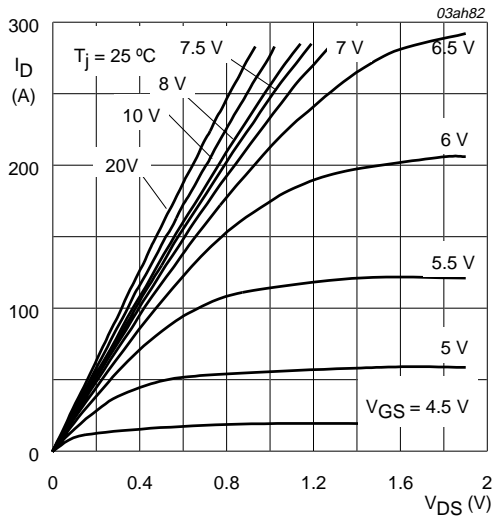


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

8. Characteristics

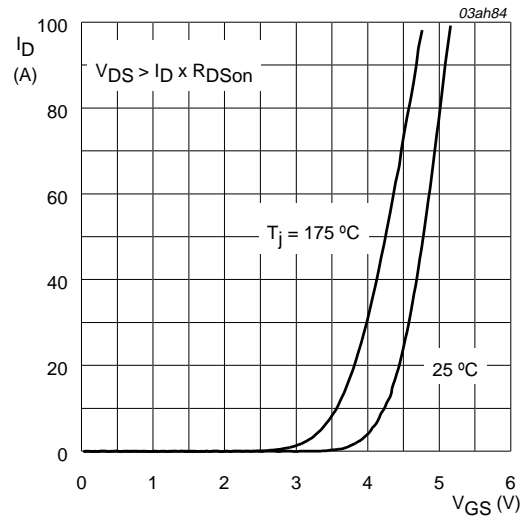
Table 5: Characteristics
 $T_j = 25\text{ °C}$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25\text{ mA}$; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$	60	-	-	V
		$T_j = -55\text{ °C}$	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$; Figure 9 $T_j = 25\text{ °C}$	2	3	4	V
		$T_j = 175\text{ °C}$	1	-	-	V
		$T_j = -55\text{ °C}$	-	-	4.4	V
I_{DSS}	drain-source leakage current	$V_{DS} = 30\text{ V}$; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$	-	0.02	1	μA
		$T_j = 175\text{ °C}$	-	-	500	μA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 20\text{ V}$; $V_{DS} = 0\text{ V}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; Figure 7 and 8 $T_j = 25\text{ °C}$	-	3.1	3.6	$\text{m}\Omega$
		$T_j = 175\text{ °C}$	-	6.5	7.55	$\text{m}\Omega$
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	$I_D = 75\text{ A}$; $V_{DD} = 48\text{ V}$; $V_{GS} = 10\text{ V}$; Figure 13	-	168	-	nC
Q_{gs}	gate-source charge		-	36	-	nC
Q_{gd}	gate-drain (Miller) charge		-	54	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$; $f = 1\text{ MHz}$; Figure 11	-	8300	-	pF
C_{oss}	output capacitance		-	1050	-	pF
C_{rss}	reverse transfer capacitance		-	550	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 15\text{ V}$; $I_D = 12\text{ A}$; $V_{GS} = 10\text{ V}$; $R_G = 6\text{ }\Omega$; resistive load	-	38	-	ns
t_r	rise time		-	74	-	ns
$t_{d(off)}$	turn-off delay time		-	133	-	ns
t_f	all time		-	75	-	ns
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; Figure 12	-	0.8	1.2	V



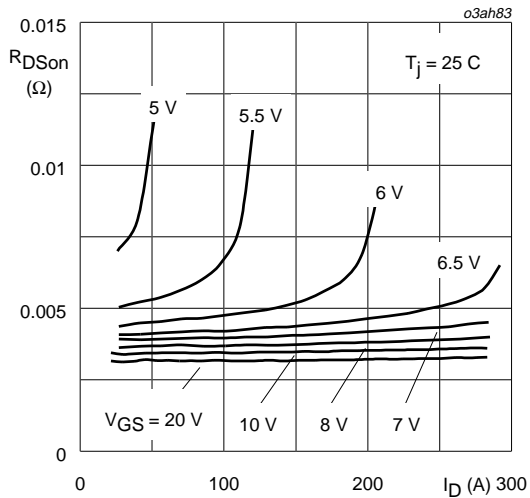
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



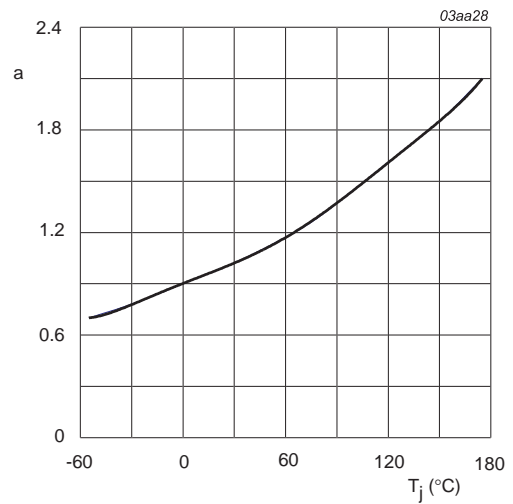
$T_j = 25\text{ }^\circ\text{C}$ and $175\text{ }^\circ\text{C}$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



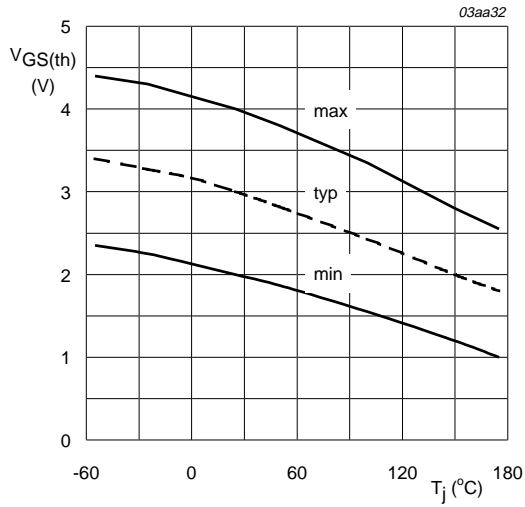
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



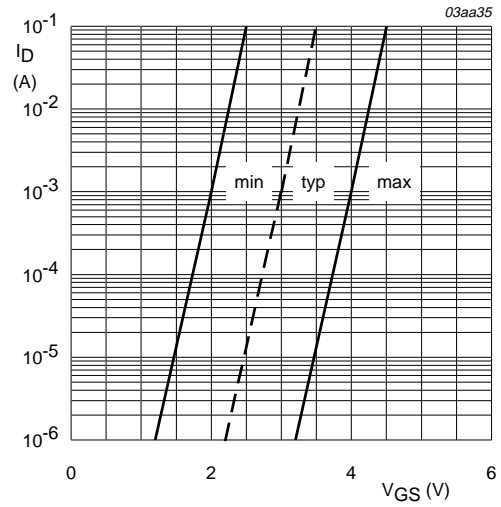
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



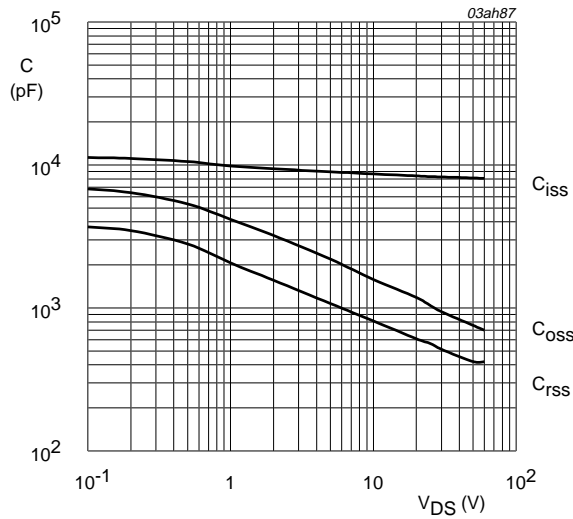
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



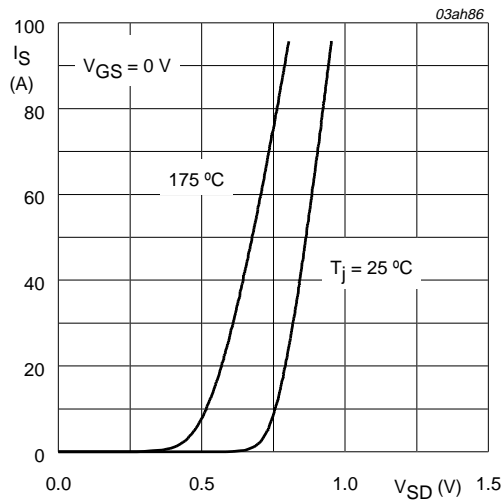
$T_j = 25 \text{ }^{\circ}C; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



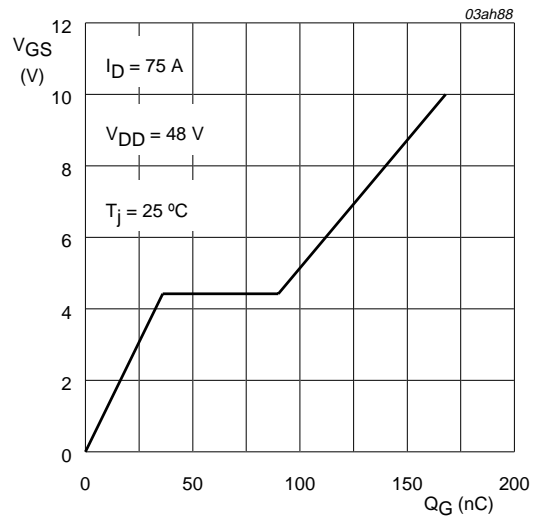
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25^\circ\text{C}$ and 175°C ; $V_{GS} = 0\text{ V}$

Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 75\text{ A}$; $V_{DD} = 48\text{ V}$

Fig 13. Gate-source voltage as a function of gate charge; typical values.

9. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

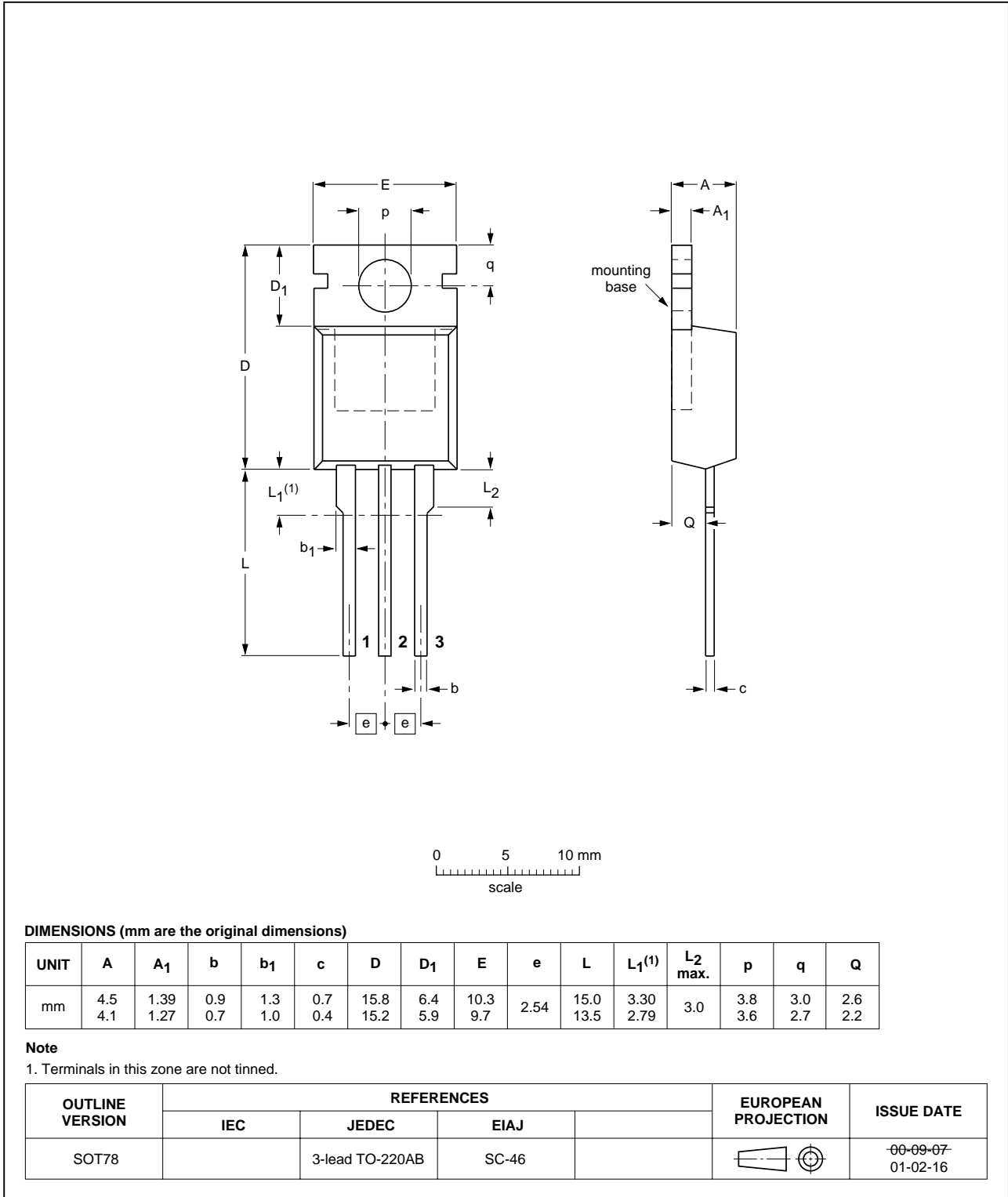


Fig 14. SOT78 (TO-220AB).

Plastic single-ended surface mounted package (Philips version of D²-PAK); 3 leads
(one lead cropped)

SOT404

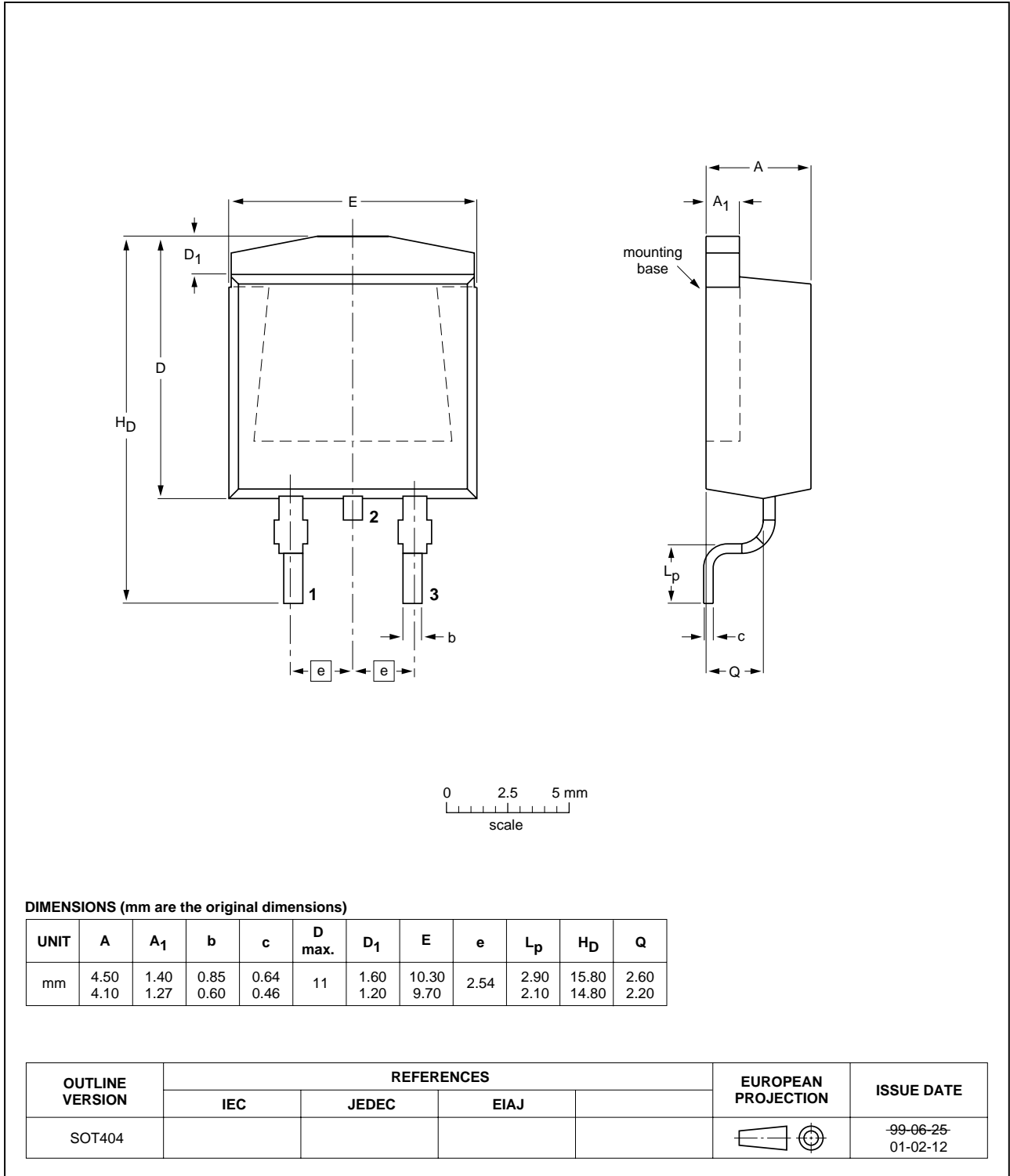


Fig 15. SOT404 (D²-PAK)

10. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
01	20020426	-	Product data; initial version

11. Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definition
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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